查询"2SA102000纳度商RANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2 S A 1 0 2 0

POWER AMPLIFIER APPLICATIONS. POWER SWITCHING APPLICATIONS.

• Low Collector Saturation Voltage

: $V_{CE(sat)} = -0.5V \text{ (Max.)}$ $(I_C = -1A)$

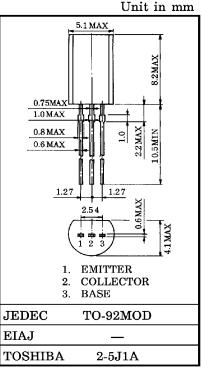
• High Speed Switching Time : $t_{stg} = 1.0 \mu s$ (Typ.)

• Complementary to 2SC2655.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	v_{CBO}	-50	v	
Collector-Emitter Voltage	v_{CEO}	-50	V	
Emitter-Base Voltage	$V_{ m EBO}$	-5	V	
Collector Current	$I_{\mathbf{C}}$	-2	Α	
Collector Power Dissipation	PC	900	mW	
Junction Temperature	T_{j}	150	°C	
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C	

INDUSTRIAL APPLICATIONS



Weight: 0.36g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -50V, I_{E} = 0$		_	-1.0	μ A
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -5V, I_C = 0$			-1.0	μ A
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	$I_{C} = -10 \text{mA}, I_{B} = 0$	-50	_	_	V
DC Current Gain		h _{FE} (1)	$V_{CE} = -2V, I_{C} = -0.5A$	70	_	240	
		h _{FE} (2)	$V_{CE} = -2V, I_{C} = -1.5A$	40	_		
Collector-Emitter Voltage	Saturation	V _{CE(sat)}	$I_C = -1A, I_B = -0.05A$	1	_	-0.5	v
Base-Emitter Saturation Voltage		$V_{\mathrm{BE(sat)}}$	$I_C = -1A$, $I_B = -0.05A$	1	_	-1.2	V
Transition Frequency		$\mathbf{f_T}$	$V_{CE} = -2V, I_{C} = -0.5A$	1	100	_	MHz
Collector Output Capacitance		$\mathrm{C_{ob}}$	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$	1	40	_	рF
Switching Time	Turn-on Time	ton	20μs 入力 I _{B2} 出力 I _{B1} I _{B1} I _{B1} I _{B2} 出力 I _{B2} I _{B1} I _{B2} I _{B1} I _{B2} I _{B1} I _{B2} I _{B1} I _{B2} I _{B2} I _{B2} I _{B1} I _{B2} I		0.1	_	
	Storage Time	t_{stg}			1.0	_	μs
	Fall Time	t_f	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	_	0.1	_	

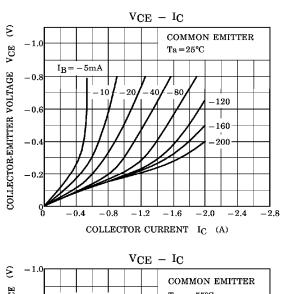
Note: hff (1) Classification $O: 70\sim140$, $Y: 120\sim240$

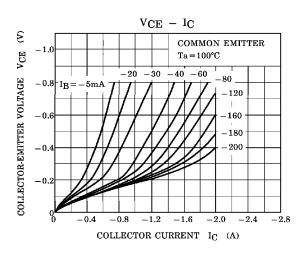
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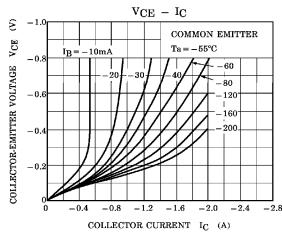
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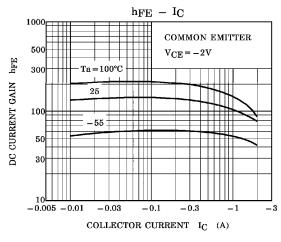
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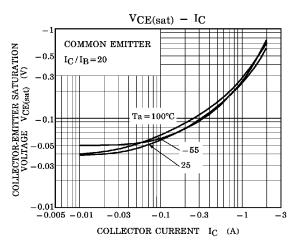
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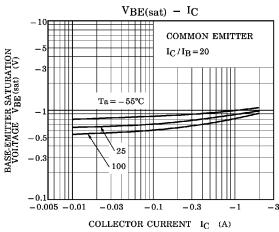










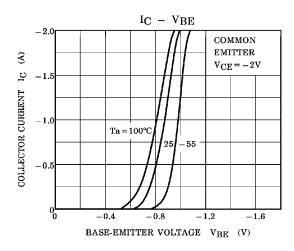


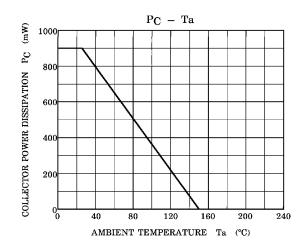
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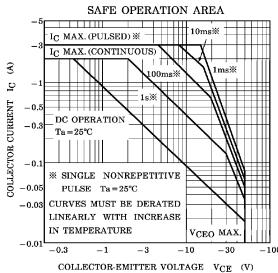
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